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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

REINHARD SCHAUER ET AL

Serial Number: 09/890,656 Group Art Unit: 2811

Filed: August 2, 2001

For: SEMICONDUCTOR WAFER COMPRISING A THIN EPITAXIAL SILICON LAYER AND METHOD FOR PRODUCING SAME

Information Disclosure Statement

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir or Madam:

I, Wolfgang Staudacher, associated with the preparation and prosecution of the above-identified application, residing at Seebauerstraße 4, 81735 München, Germany, wish to call the attention of the Patent Examiner to the references enumerated on the enclosed PTO Form-1449.

I believe the documents enumerated on the enclosed Form PTO-1449 and attached thereto, are cited in the enclosed application, in the Office Action of the German Patent and Trademark Office and in the International Search Report and may be material to the examination of the application.

Therefore, it is respectfully requested that the foregoing Information Disclosure Statement be considered by the Examiner and incorporated into the file of this application.

I wish to comment as follows concerning the prior art references enumerated on PTO Form-1449:

For DE 198 23 962 an English Derwent Abstract is enclosed.

For EP 0 725 169 an English Derwent Abstract is enclosed.

Electrochemical Society Proceedings, Volume 98-1, pp. 855-861 is already in English language.

Jpn. J. Appl. Phys. Vol. 36, 1997, pp. 2565-2570 is already in English language.

Lee, S. K. et al.: Silicon epitaxial growth by rapid thermal processing chemical vapor deposition in: Appl. Phys. Lett.; 1989, vol. 54 (18), pp. 1775-1777 is already in English language.

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Skelly, G and Adams, A.C.: Impurity Atom Transfer during Epitaxial Deposition of Silicon, in: J. Electrochemical Soc., 1973, vol. 120, pp. 116-122 is already in English language.

SZE, S. M.: Physics of Semiconductor Devices, New York, Wiley, 1969, p. 43 is already in English language.

Ohshita, Y. et al.: Surface reaction mechanism of SiCl₂ with carrier gas H₂ in silicon vapor phase epitaxial growth in: Journal of Crystal Growth, 1991, vol. 108, pp. 499-507 is already in English language.

Hammond, M. L.: Silicon Epitaxy in: Solid State Technology, 1978, H. 11, pp. 68-75 is already in English language.

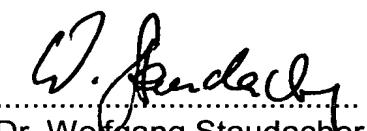
Bloem J. and Claassen, W.A.P.: Nucleation and growth of silicon films by chemical vapour deposition in: Philips Tech. Rev., 1983/84, vol. 41, no. 2, pp. 60-69 is already in English language.

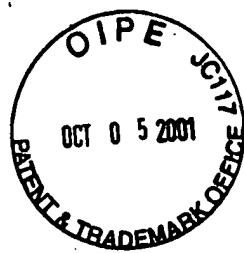
EP 0 959 154 is already in English lanugage.

EP 0 644 588 is already in English language.

For EP 0 829 559 the corresponding US 5,935,320.

Signed this 10th day of August, 2001.


Dr. Wolfgang Staudacher



PATENT

UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: SCHAUER ET AL-PCT

SERIAL NO: 09/890,656 EXAMINER:

FILED: AUGUST 2, 2001 GROUP: 2811

TITLE: SEMICONDUCTOR WAFER WITH A THIN EPITAXIAL SILICON LAYER, AND METHOD FOR PRODUCING SAME

SUBMISSION OF INFORMATION DISCLOSURE STATEMENT
OF DR. WOLFGANG STAUDACHER

ATT: BOX NON FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Applicants wish to bring to the attention of the Patent Examiner the attached Information Disclosure Statement, duly signed by Dr. Wolfgang Staudacher and the sixteen (16) references listed on the enclosed Form PTO-1449 and attached thereto.

The relevance of these references is that they are cited in the present patent application, in the Office Action of the German Patent and Trademark Office and in the International Search Report and may be material to the examination of the application.

Since this Information Disclosure Statement is being filed prior to a first Office Action, it is believed that no fee is

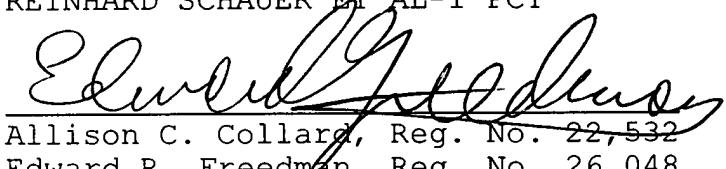
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due. However, if it is determined that a fee is due, the Commissioner is hereby authorized to charge, or to credit any over payment, to our Deposit Account Number 03-2468.

It is respectfully requested that this Information Disclosure Statement be considered and placed into the application file.

Respectfully submitted,

REINHARD SCHAUER ET AL-1 PCT


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Edward R. Freedman, Reg. No. 26,048
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- Enclosures:
- 1) Information Disclosure Statement Of DR. WOLFGANG STAUDACHER
 - 2) PTO-form 1449 w/copies of 16 references
 - 3) Copy of the Office Action of the German Patent and Trademark Office
 - 4) Copy of International Search Report

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: ASSISTANT COMMISSIONER OF PATENTS, Washington, D.C. 20231, on October 2, 2001


Lisa L. Vulpis